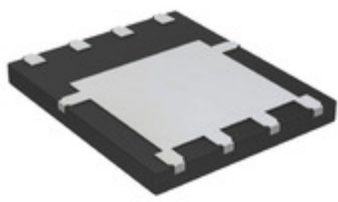


	<h2 style="color: #D9534F;">SIDR638DP-T1-GE3</h2>
	Hersteller-Teilenummer: SIDR638DP-T1-GE3
	Hersteller / Marke: Electro-Films (EFI) / Vishay
	Teil der Beschreibung: MOSFET N-CH 40V 100A SO-8
	Datenblätter: <ul style="list-style-type: none">  1.SIDR638DP-T1-GE3.pdf  2.SIDR638DP-T1-GE3.pdf
	RoHs Status: Bleifrei / RoHS-konform
	Lagerzustand: New original, 2676 pcs Stock Available.
	Liefern von: Hong Kong
	Versandweg: DHL/Fedex/TNT/UPS/EMS
<p>Image may be representation. See specs for product details.</p>	

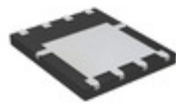
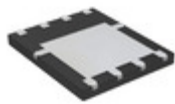
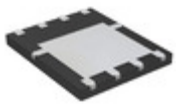
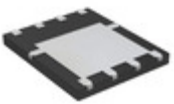
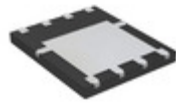
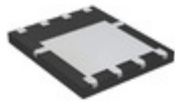
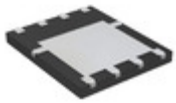
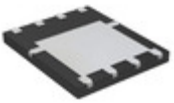
Spezifikationen

Teilenummer	SIDR638DP-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 40V 100A SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	2676 pcs Stock
VGS (th) (Max) @ Id	2.3V @ 250µA
Vgs (Max)	+20V, -16V
Technologie	MOSFET (Metal Oxide)
Supplier Device-Gehäuse	PowerPAK® SO-8DC
Serie	TrenchFET® Gen IV
Rds On (Max) @ Id, Vgs	0.88 mOhm @ 20A, 10V
Verlustleistung (max)	125W (Tc)
Verpackung	Tape & Reel (TR)
Verpackung / Gehäuse	PowerPAK® SO-8
Andere Namen	SIDR638DP-T1-GE3TR
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Eingabekapazität (Ciss) (Max) @ Vds	10500pF @ 20V
Gate Charge (Qg) (Max) @ Vgs	204nC @ 10V
Typ FET	N-Channel
FET-Merkmal	-
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Drain-Source-Spannung (Vdss)	40V
detaillierte Beschreibung	N-Channel 40V 100A (Tc) 125W (Tc) Surface Mount
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	100A (Tc)

SIDR638DP-T1-GE3 Electronic Components ist ein 100% neues Original von YIC Distributor, SIDR638DP-T1-GE3-Datenblätter durchsuchen, PDF, Inventar bei Y-IC.com Online, SIDR638DP-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen bestellen. Versand per DHL / FedEx / TNT / UPS Express. Unterstützung der Zahlung mit telegrafischer Überweisung (T / T) oder PayPal.

RFQ SIDR638DP-T1-GE3 E-Mail: Info@Y-IC.com

Sie können auch interessiert

 <p>SIDR140DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CHAN 25V PPAK SO-8DC</p>	 <p>SIDR402DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CHAN 40V PPSO-8DC</p>	 <p>SIDR392DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CHAN 30V</p>	 <p>SIDR668DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 100V</p>
 <p>SIDR610DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CHAN 200V PPAK SO-8DC</p>	 <p>SIDR622DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CHAN 150V</p>	 <p>SIDR626DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CHAN 60V</p>	 <p>SIDR870ADP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 100V 95A SO-8</p>

SIDR638DP-T1-GE3 Zugehöriges

Mehr

Schlüsselwort

SIDR638DP-T1-GE3 Electronic Components (EFI) / Vishay	SIDR638DP-T1-GE3 Datenblatt	SIDR638DP-T1-GE3-Datenblätter	SIDR638DP-T1-GE3 PDF	Electro-Films (EFI) / Vishay SIDR638DP-T1-GE3
SIDR638DP-T1-GE3 Electronic	SIDR638DP-T1-GE3-Komponenten	SIDR638DP-T1-GE3-Verteiler	SIDR638DP-T1-GE3-Bild	SIDR638DP-T1-GE3-Teil
SIDR638DP-T1-GE3 Preis	SIDR638DP-T1-GE3 Hersteller	SIDR638DP-T1-GE3 Bild	SIDR638DP-T1-GE3 Aktie	SIDR638DP-T1-GE3 Inventar
SIDR638DP-T1-GE3 Neu	SIDR638DP-T1-GE3 Original	SIDR638DP-T1-GE3 garantiert	SIDR638DP-T1-GE3 RFQ	SIDR638DP-T1-GE3 Online bestellen

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr. 509, 5 / F Sing Win-Fabrikgebäude, 15-17 Shing Yip Street, Kwun Tong, Kowloon, Hongkong.

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